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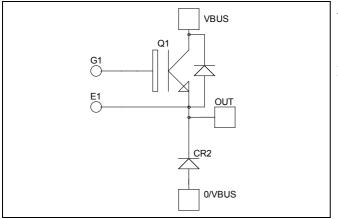


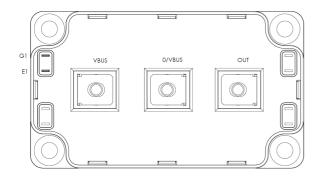


APTGT150SK120G

 $I_{C} = 150A$ @ $T_{c} = 80^{\circ}C$

Buck chopper Fast Trench + Field Stop IGBT3 Power Module





Application

- AC and DC motor control
- Switched Mode Power Supplies

 $V_{CES} = 1200V$

Features

- Fast Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
 - Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	220	
I _C	Continuous Conector Current	$T_C = 80^{\circ}C$	150	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	350	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	690	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	300A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				350	μA
V _{CE(sat)}	Collector Emitter Saturation Voltage	J J J J J J J J J J J J J J J J J J J	$T_j = 25^{\circ}C$		1.7	2.1	V
			$T_{j} = 125^{\circ}C$		2.0		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			10.7		
C _{oes}	Output Capacitance	$V_{CE} = 25V$ f = 1MHz			0.56		nF
C _{res}	Reverse Transfer Capacitance				0.48		
T _{d(on)}	Turn-on Delay Time		Inductive Switching (25°C)		280		
Tr	Rise Time	$V_{GE} = \pm 15V$			40		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 150A$	$V_{Bus} = 600V$		420		ns
$T_{\rm f}$	Fall Time	$R_{\rm G} = 2.2\Omega$			75		
T _{d(on)}	Turn-on Delay Time	Inductive Swite	ching (125°C)		290		
Tr	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_{C} = 150A$ $R_{G} = 2.2\Omega$			45		ns
T _{d(off)}	Turn-off Delay Time				520		
$T_{\rm f}$	Fall Time				90		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125^{\circ}C$		14		mJ
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$I_{\rm C} = 150 \text{A}$ $R_{\rm G} = 2.2 \Omega$	$T_{j} = 125^{\circ}C$		16		111)

Chopper diode ratings and characteristics

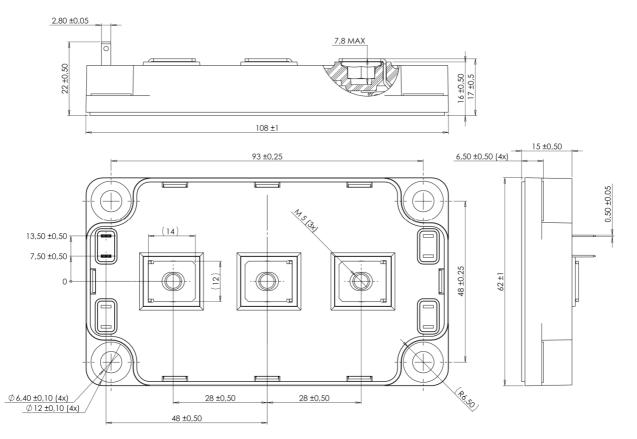
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$			250	μA
*Kivi			$T_{j} = 125^{\circ}C$			600	<i>p</i> 41 1
$I_{\rm F}$	DC Forward Current		$Tc = 80^{\circ}C$		150		А
V _F	Diode Forward Voltage	$I_{\rm F} = 150 {\rm A}$	$T_i = 25^{\circ}C$		1.6	2.1	V
• F	Blode Forward Voluge		$T_i = 125^{\circ}C$		1.6		•
t _{rr}	Reverse Recovery Time	$I_F = 150A$ $V_R = 600V$ $di/dt = 2500A/\mu s$	$T_j = 25^{\circ}C$		170		ns
۹r			$T_{j} = 125^{\circ}C$		280		115
Q _{rr}	Reverse Recovery Charge		$T_j = 25^{\circ}C$		14		uС
Qrr			$T_{j} = 125^{\circ}C$		28		μC
Er	Reverse Recovery Energy		$T_i = 25^{\circ}C$		6		mJ
Lr	Reverse Receivery Energy		$T_{j} = 125^{\circ}C$		11		1113



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance IGBT Diode		IGBT			0.18	°C/W
R _{th} JC			Diode			0.30	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	19.111
Wt	Package Weight					300	g

SP6 Package outline (dimensions in mm)



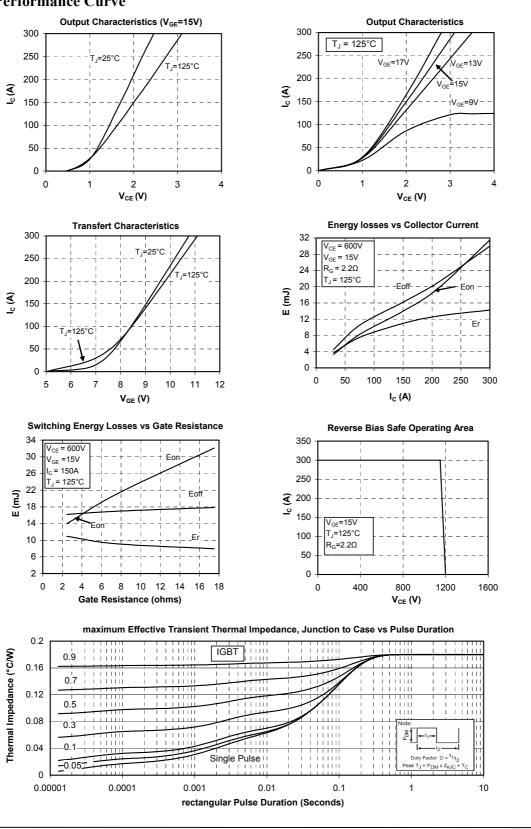
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

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Typical Performance Curve

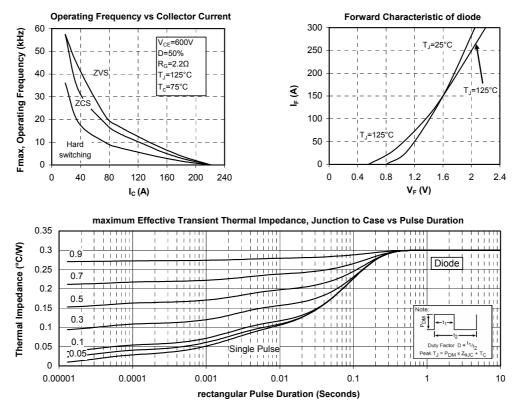
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